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Microsemi.

# Power Matters<sup>™</sup>

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### 2N7377 (#23647)

## Products

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### Overview Diagrams

Electrical Rating

Symbol

Min

Typ

Max

Unit

Collector to Emitter Saturation Voltage

V<sub>CE(sat)</sub>

DC Current Gain

HFE

25.00

75.00

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			400.00	V
Collector Current (dc)	I <sub>C</sub>			5.00	А
Collector-Emitter Voltage (Base Open)	V <sub>CEO</sub>			300.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			6.00	V
Power Dissipation, Total	P <sub>T</sub>			58.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT( BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ NPN Transistor

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